

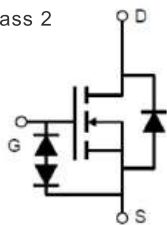
# MJ N-Channel Super Trench Power MOSFET

### Description

The MJXP3085EG uses Super Trench technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

## General Features

- ◆  $V_{DS}=30V, I_D=85A$   
 $R_{DS(ON)}=2.7m\Omega$  (typical) @  $V_{GS}=10V$   
 $R_{DS(ON)}=3.5m\Omega$  (typical) @  $V_{GS}=4.5V$
- ◆ Excellent gate charge x  $R_{DS(on)}$  product(FOM)
- ◆ Very low on-resistance  $R_{DS(on)}$
- ◆ 150°C operating temperature
- ◆ Pb-free lead plating
- ◆ 100% UIS tested
- ◆ ESD protection : HBM Class 2



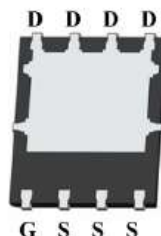
### Schematic Diagram

## Application

- ◆ DC/DC Converter
- ◆ Ideal for high-frequency switching and synchronous rectification



Top View



Bottom View

100% UIS TESTED! 100%  $\Delta V_d$ s TESTED!

## Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
MJXP3085EG	MJXP3085EG	DFN5X6-8L	-	-	-

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	30	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous (Silicon Limited)	I <sub>D</sub>	85	A
Drain Current-Continuous (T <sub>c</sub> =100°C)	I <sub>D(100°C)</sub>	60	A
Pulsed Drain Current (Package Limited)	I <sub>DM</sub>	200	A
Maximum Power Dissipation	P <sub>D</sub>	65	W
Derating factor		0.52	W/°C
Single pulse avalanche energy <sup>(Note 5)</sup>	E <sub>AS</sub>	352	mJ
Operating Junction and Storage Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-55 To 150	°C

### Thermal Characteristic

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	R <sub>θJC</sub>	1.92	°C/W
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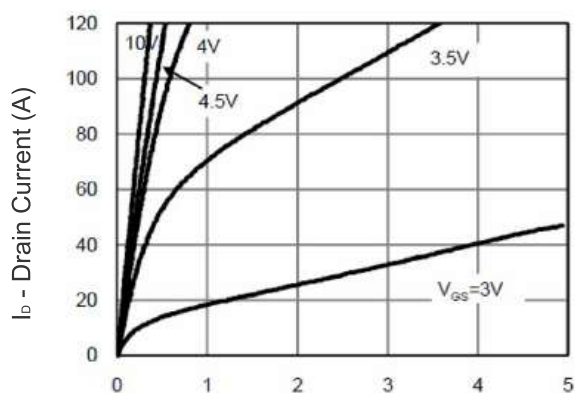
Electrical Characteristics (T<sub>c</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	30	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±10	μA
On Characteristics <small>(Note 3)</small>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250μA	1.2	-	2.2	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =40A	-	2.7	3.0	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =40A	-	3.5	3.8	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V,I <sub>D</sub> =40A	-	30	-	S
Dynamic Characteristics <small>(Note 4)</small>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =15V,V <sub>GS</sub> =0V F=1.0MHz	-	2200	2640	PF
Output Capacitance	C <sub>oss</sub>		-	807	906	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	22.7	27	PF
Switching Characteristics <small>(Note 4)</small>						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =15V,I <sub>D</sub> =40A V <sub>GS</sub> =10V,R <sub>G</sub> =1.6Ω	-	8	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	4.5	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	29	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	8.5	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =15V,I <sub>D</sub> =40A V <sub>GS</sub> =10V	-	34.6	38	nC
Gate-Source Charge	Q <sub>gs</sub>		-	7.8	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	3.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage <small>(Note 3)</small>	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =40A	-	-	1.2	V
Diode Forward Current <small>(Note 2)</small>	I <sub>S</sub>		-	-	85	A
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> =25°C, I <sub>F</sub> =I <sub>S</sub> di/dt=500A/μs <small>(Note 3)</small>	-	16	-	nS
Reverse Recovery Charge	Q <sub>rr</sub>		-	35	-	nC

Notes:

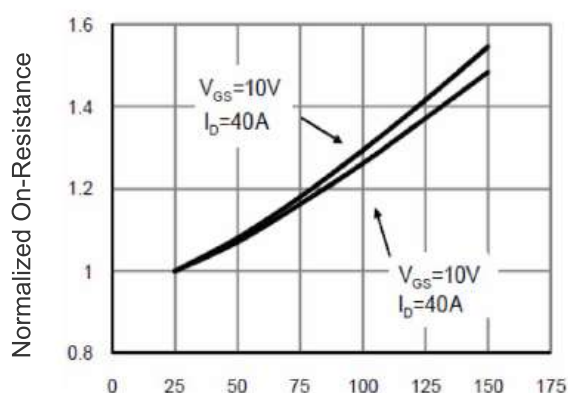
- ① Repetitive Rating: Pulse width limited by maximum junction temperature.
- ② Surface Mounted on FR4 Board, t ≤ 10 sec.
- ③ Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
- ④ Guaranteed by design, not subject to production
- ⑤ EAS condition: T<sub>J</sub>=25°C, V<sub>DD</sub>=15V,V<sub>G</sub>=10V,L=0.5mH,R<sub>G</sub>=25Ω

## Typical Electrical and Thermal Characteristics



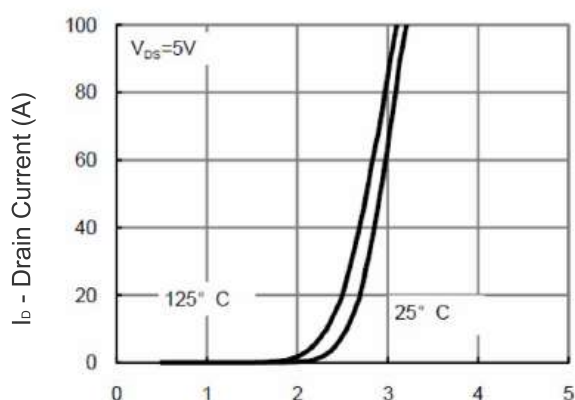
V<sub>ds</sub> Drain-Source Voltage (V)

Figure 1 Output Characteristics



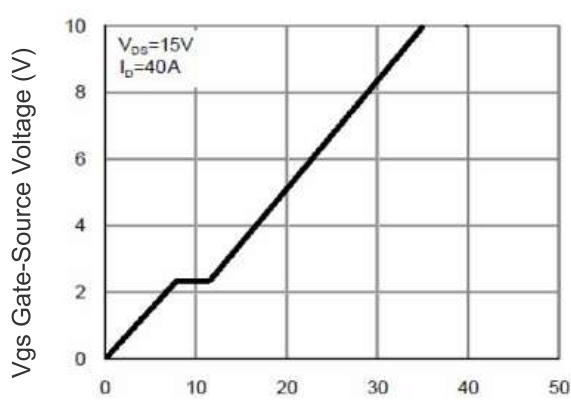
T<sub>J</sub> -Junction Temperature(°C)

Figure 4 Rdson-Junction Temperature



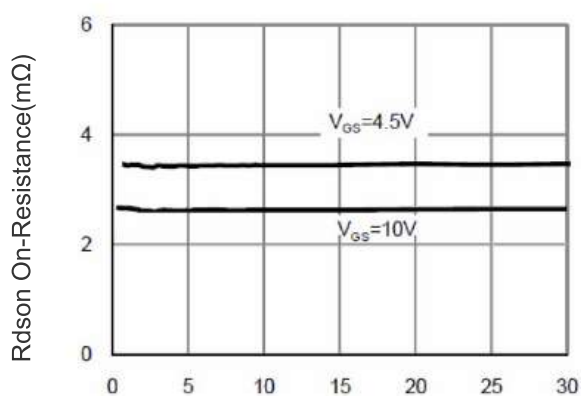
V<sub>gs</sub> Gate-Source Voltage (V)

Figure 2 Transfer Characteristics



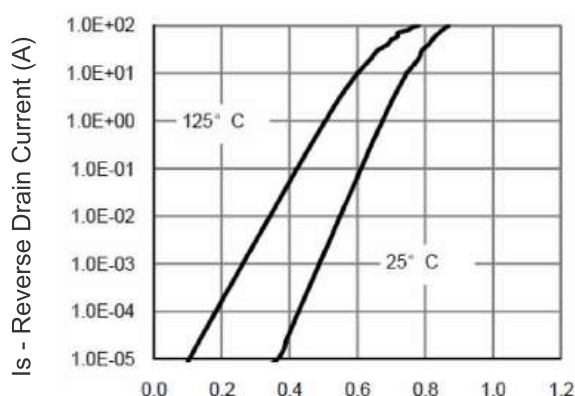
Q<sub>g</sub> Gate Charge (nC)

Figure 5 Gate Charge



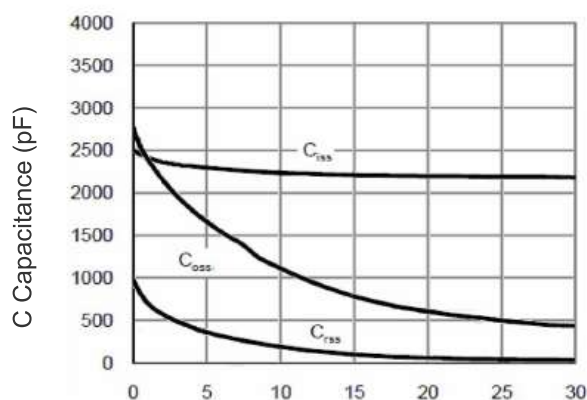
I<sub>D</sub> - Drain Current (A)

Figure 3 Rdson- Drain Current



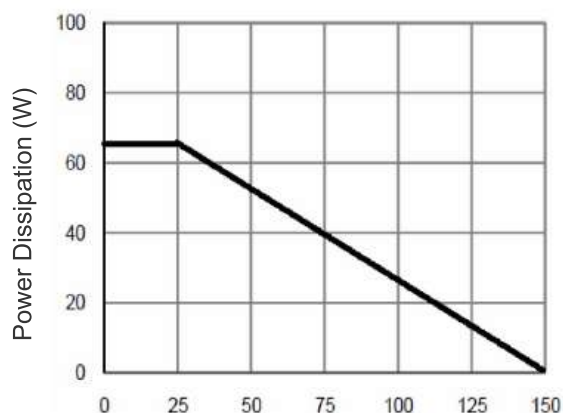
V<sub>sd</sub> Source-Drain Voltage (V)

Figure 6 Source- Drain Diode Forward



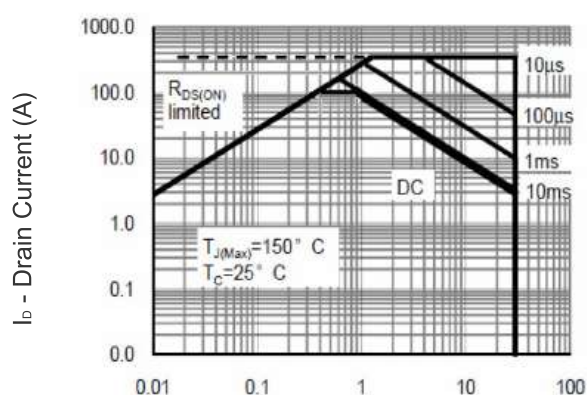
Vds Drain-Source Voltage (V)

Figure 7 Capacitance vs Vds



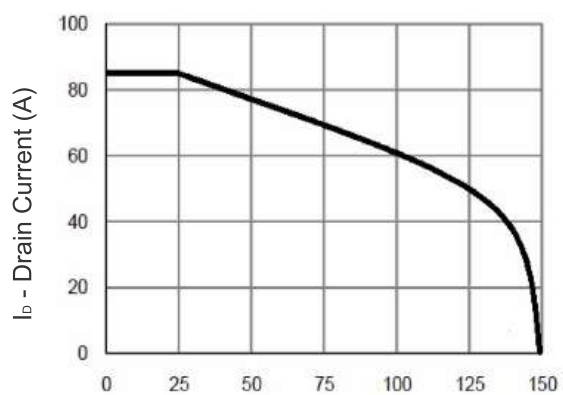
Tj -Junction Temperature(°C)

Figure 9 Power De-rating



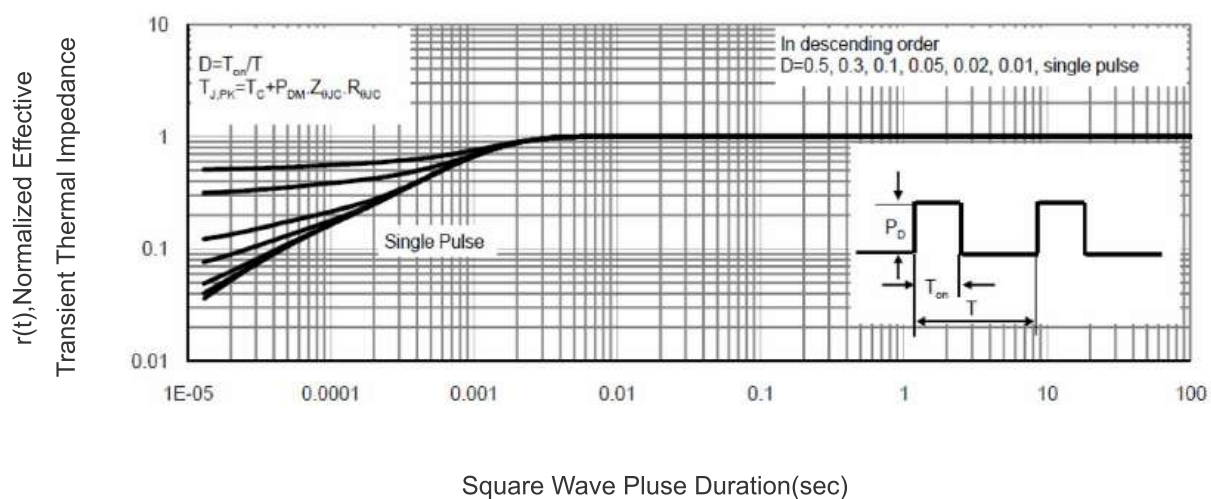
Vds Drain-Source Voltage (V)

Figure 8 Safe Operation Area



Tj -Junction Temperature(°C)

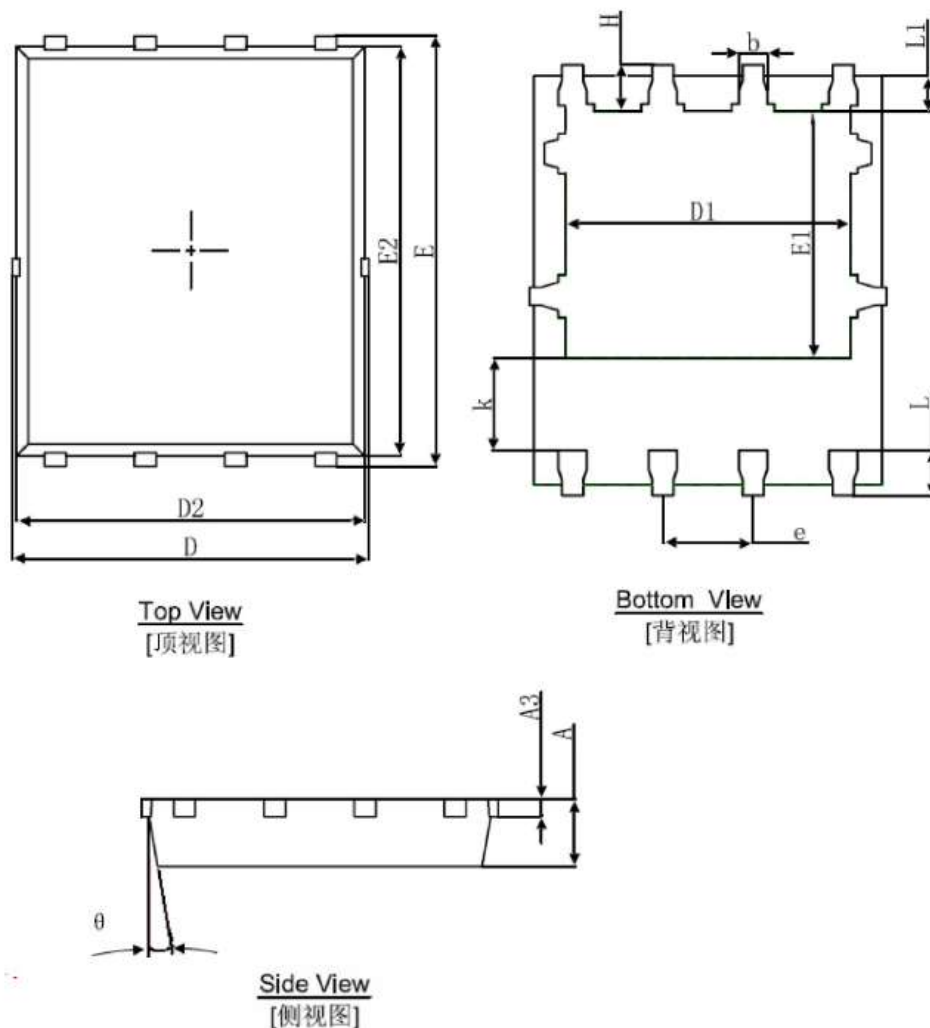
Figure 10 Current De-rating



Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance

## DFN5X6-8L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
$\theta$	8°		8°	
	12°		12°	



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